

AlGaInP/GaAs Yellow Green Chip ---TK0508YGN

1. Scope

- The specification applies to AlGaInP LED chips.
- Type : TK0508YGN.

2. Structure

- AlGaInP/GaAs yellow green LED chip.
- Electrode P (anode) side : Aluminum or Gold.
- Electrode N (cathode) side : Gold alloy.

3. Size

- Chip size : 200 μm \times 200 μm
- Chip height : 180 μm \pm 30 μm
- Pattern drawing : per fig. 1

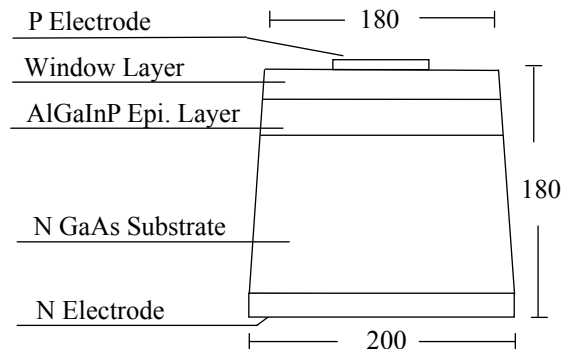
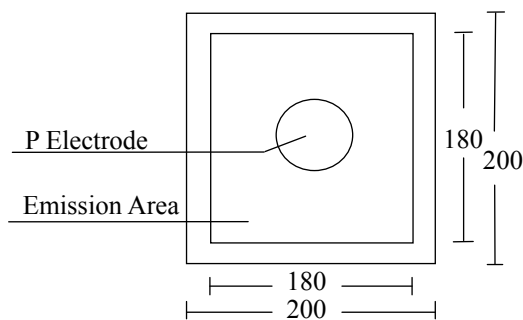
4. Electro-Optical Characteristics

($T_a = +25^\circ\text{C}$)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	V_F	$I_F = 20\text{ mA}$		2.00	2.30	V
Reverse Voltage	V_R	$I_R = 10\ \mu\text{A}$	5			V
Luminous Intensity	I_V	$I_F = 20\text{ mA}$		※		mcd
Wavelength	λ_p / λ_d	$I_F = 20\text{ mA}$		575/572		nm
Spectrum Width of Half Value	$\Delta \lambda$	$I_F = 20\text{ mA}$		20		nm

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- Rank C : $I_V \text{ min.} \geq 10.0$
 - Rank D : $I_V \text{ min.} \geq 20.0$
 - Rank E : $I_V \text{ min.} \geq 30.0$
 - Rank F : $I_V \text{ min.} \geq 40.0$

- Rank G : $I_V \text{ min.} \geq 50.0$
- Rank H : $I_V \text{ min.} \geq 60.0$



Unit : μm

fig. 1

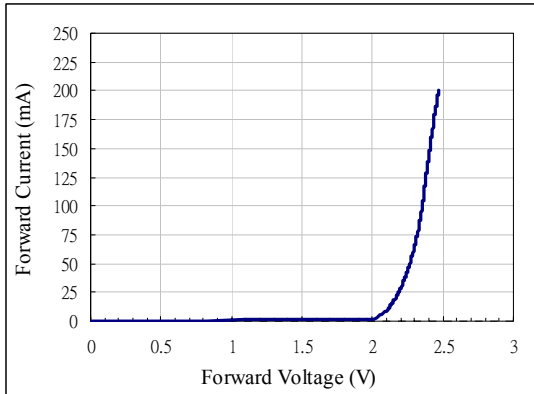
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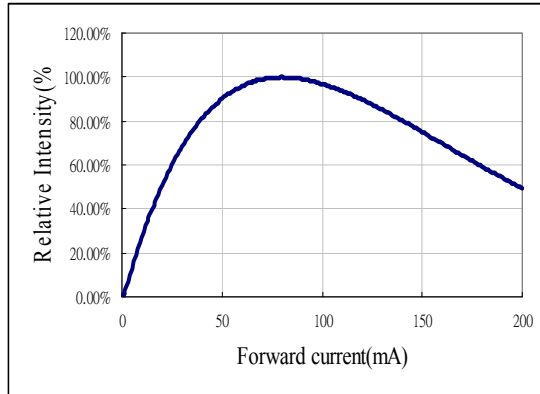
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Electro-Optical Characteristics Curve

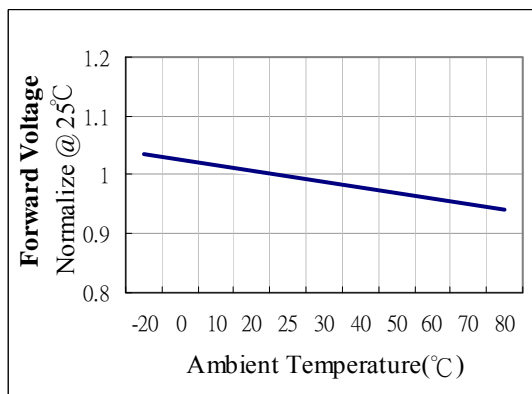
Forward current vs. Forward voltage



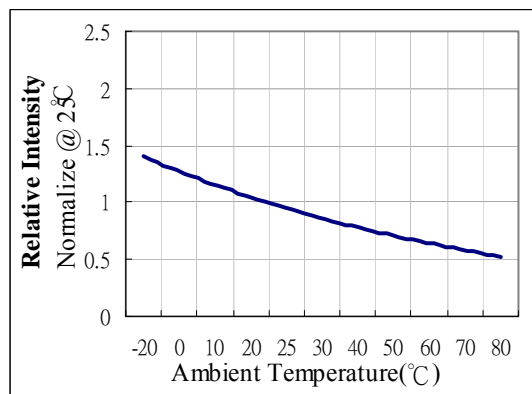
Relative intensity vs. Forward current



Forward voltage vs. Temperature



Relative intensity vs. Temperature



Relative intensity vs. Wavelength

